



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

2SB1218A TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 150 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -100 mA

Collector-base voltage

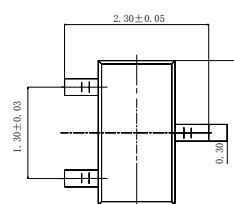
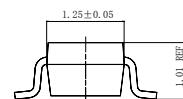
$V_{(BR)CBO}$: -45 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-45			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-2mA, I_B=0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10V, I_C=-2mA$	160		460	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-1mA, f=200MHz$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		2.7		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	160-260	210-340	290-460
Marking	BQ1	BR1	BS1